

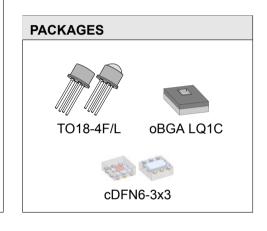
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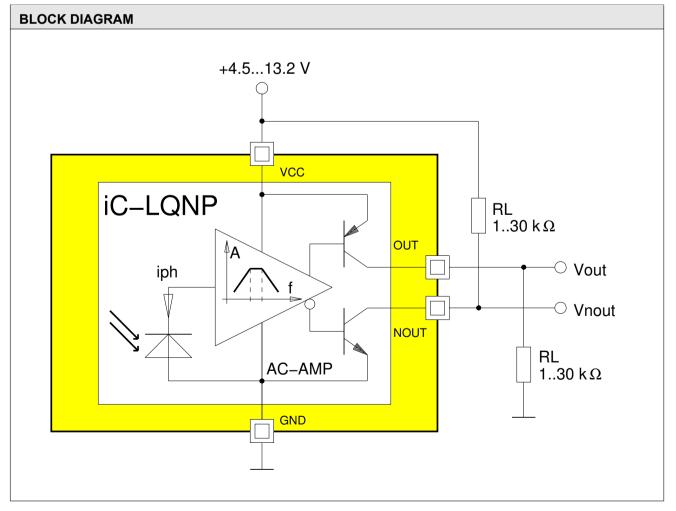
### FEATURES

- Fast response amplifier with on-chip photodiode
- High interference immunity due to monolithic design
- ♦ Active photodiode area of ca. 1 mm<sup>2</sup>
- Suitable for visible light and near infra-red
- ♦ Integrated band-pass filter with 140 kHz center frequency
- Maximum gain obtained for pulse light of 1.4 µs and upwards
- High LF and DC (ambient) light suppression
- Transfer characteristics irrespective of ambient light level
- Soft signal and noise limiter with excess ambient light
- ♦ Fast recovery from flashes
- Complementary analog current source outputs, transimpedance can be set by external resistor
- Single 5 to 12 V supply, low power consumption also with bright ambient light

### APPLICATIONS

 Receiver for through beam and reflection light barriers with background suppression (sunlight) e.g. for presence detection in power operated gates, doors and windows etc.







### DESCRIPTION

iC-LQNP is a sensor for pulse and alternating light with a monolithically integrated photodiode. The device supersedes conventional photoreceivers, such as those in light barriers, for example.

Changes in the photocurrent are amplified whereas the photocurrents caused by background light are electronically suppressed with over 60 dB (at 100 Hz).

The integrated amplifier forms a band-pass characteristic without using any external components. The high pass filter suppresses ambient light and low frequency alternating light and the low pass filter reduces high frequency noise. For visible light or near infrared the highest sensitivity for alternating light signals is reached at approximately 140 kHz; for pulse light this is reached at  $1.4 \,\mu$ s and upwards.

The transimpedance can be selected within a range of approximately 1 to  $10 M\Omega$  via the external load resistor.

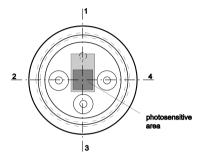
iC-LQNP is available as a 4-lead TO18 metal can package with a glass lens or flat window. Customised COB versions are also possible.



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### PACKAGING INFORMATION TO18-4F/L, cDFN6, oBGA LQ1C

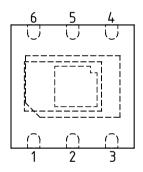
### **PIN CONFIGURATION TO18-4F/L**



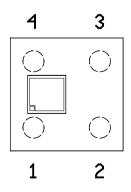
#### PIN FUNCTIONS No. Name Function

- 1 GND Ground
- 2 OUT High-Side Current Output
- 3 VCC +4.5 to +13.2 V Supply Voltage
- 4 NOUT Low-Side Current Output

#### PIN CONFIGURATION cDFN6 3 mm x 3 mm



### PIN CONFIGURATION oBGA LQ1C



### PIN FUNCTIONS

### No. Name Function

- 1 GND Ground
- 2 OUT High-Side Current Output
- 3 n.c.
- 4 n.c.
- 5 NOUT Low-Side Current Output
- 6 VCC +4.5 to +13.2 V Supply Voltage

# PIN FUNCTIONS

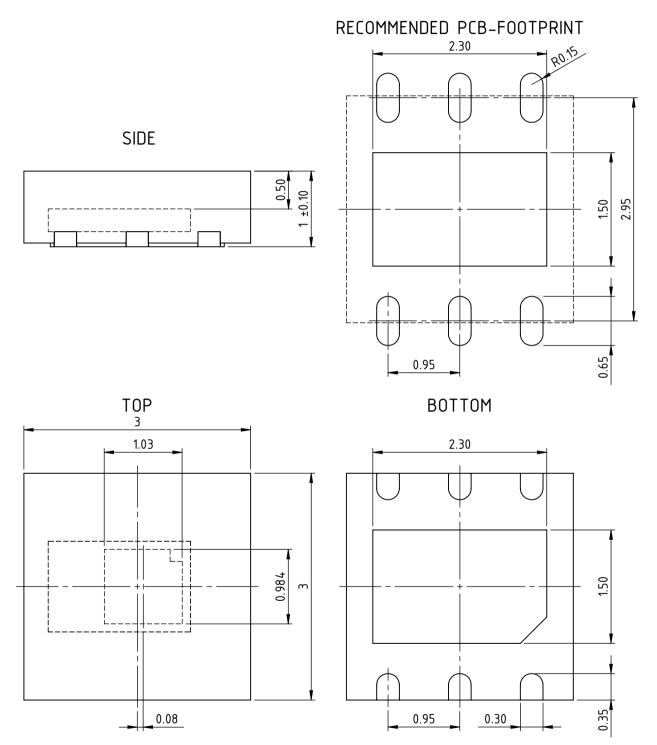
# No. Name Function

- 1 GND Ground
- 2 VCC +4.5 to +13.2 V Supply Voltage
- 3 OUT High-Side Current Output
- 4 GND Ground



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### PACKAGE DIMENSIONS cDFN6-3x3



All dimensions given in mm. Tolerances of form and position according to JEDEC MO-229. Positional tolerance of sensor pattern: ±0.10mm / ±1° (with respect to backside pad). drb\_cdfn6-3x3-1\_lqn\_pack\_1, 20:1



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### **ABSOLUTE MAXIMUM RATINGS**

Beyond these values damage may occur; device operation is not guaranteed.

Item	Symbol	Parameter	Conditions			Unit
No.	-			Min.	Max.	
G001	VCC	Supply Voltage		0	15	V
G002	l()	Output Current		-4	4	mA
G003	Vd()	ESD susceptibility at all pins	HBM, 100 pF discharged through $1.5 \text{ k}\Omega$		1.5	kV
G004	Tj	Junction Temperature		-40	150	°C
G005	Ts	Storage Temperature	see package specifications			

### THERMAL DATA

Operating Conditions: VCC = 4.5...13.2 V

Item	m Symbol Parameter Conditions		[				
No.				Min.	Тур.	Max.	
T01	Та	Operating Ambient Temperature Range	cDFN6	0		70	°C
			for other packages, see relevant package specifications				
T02	Tpk		tpk < 10 s, convection reflow MSL6, TOL (max. floor life 8 h at 30 °C and 60% RH)			245	°C
			See Customer Information #7 for detailed information.				



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# ELECTRICAL CHARACTERISTICS

ltem	Symbol	Parameter	, CL = 20 pF, $\lambda$ = 875 nm, Tj = -25125 °C, if not c Conditions	Ì			Unit
No.				Min.	Тур.	Max.	
Total	Device	7					
001	VCC	Permissible Supply Voltage		4.5		13.2	V
002	I(VCC)	Supply Current	E(PD) = 0 E(PD)ac = 0, E(PD)pk = 0, $E(PD)cw = 30 \text{ mW/cm}^2, \text{ no load}$	0.4	0.8	1.4 2	mA mA
003	Vs(OUT)	Output Saturation Voltage at OUT	I() = -1 mA, Vs(OUT) = VCC - V(OUT)			0.5	V
004	Vs(NOUT)	Output Saturation Voltage at NOUT	I() = 1 mA			0.5	V
005	I()	Permissible Output Current in NOUT, OUT	I(NOUT) I(OUT)	0 -2		2 0	mA mA
006	10()	Output Bias Current in OUT	E(PD) = 0 E(PD) = 0, VCC = 5 V, Tj = 27 °C	-235	-145	-105	μΑ μΑ
007	10()	Output Bias Current in NOUT	E(PD) = 0 E(PD) = 0, VCC = 5 V, Tj = 27 °C	105	145	235	μΑ μΑ
008	Vc()hi	Output Clamp Voltage hi	Vc()hi = V(OUT) - VCC, VCC = 0V, I() = 4 mA	0.25	0.5	1.4	V
009	Vc()lo	Output Clamp Voltage lo	I() = -4 mA	-1.4	-0.5	-0.25	V
Photo	diode	·					·
101	Aph()	Radiant Sensitive Area		1		mm <sup>2</sup>	
102	$S(\lambda)$ max	Spectral Sensitivity			0.5		A/W
103	$\lambda_{ar}$	Spectral Application Range	$Se(\lambda_{ar}) = 0.1 \times S(\lambda)max$	500		1050	nm
Photo	current Am	plifier					
201	E()cw	Permissible DC Irradiance	$\lambda_{\text{LED}}$ für S( $\lambda$ )max, iC-LQNP Chip			30	mW/ cm <sup>2</sup>
202	Ev()cw	Ambient Light Susceptibility	standard illuminant A, T = 2856 K; TO18-4F		50		mW/ cm <sup>2</sup>
			TO18-4L		7		mW/ cm <sup>2</sup>
203	Ev()cw	Ambient Light Susceptibility	standard illuminant A, T = 2856 K;				
			TO18-4F TO18-4L		70 10		klx klx
204	E()pk	Permissible Peak Irradiance	I((N)OUT)  increases or remains constant as		10		KIX
204		r ennissible r eak madiance	E()pk increases;				
			chip, TO18-4F			100	mW/
			TO18-4L			15	cm² mW/
						15	cm <sup>2</sup>
205	Gpk	Pulse Light Amplification 875 nm	VCC = 5 V, E(PD)pk = $35 \mu$ W/cm <sup>2</sup> ,				
			$tr = tf = 0.1 \mu s$ , $twpk = 1.4 \mu s$ ;	100		0.50	
			chip, TO18-4F TO18-4L	100 700	220 1540	350 2500	A/W A/W
206	Gpk	Pulse Light Amplification 850 nm	see 205;	100		2000	,
			chip, TO18-4F TO18-4L		250 1800		A/W A/W
207	Δt()	Output Current Delay	see 205,  I((N)OUT) : 0 $\rightarrow$ 50% peak value			1.5	μs
208	trec	Recovery Time	see 205, settled better 10% to initial quiescent point			15	μs
209	trec	Power Flash Recovery Time	$E(PD)pk = 35 \text{ mW/cm}^2$ , twpk = 100 µs			60	μs
210	Gac	AC Light Amplification	f = fc, E(PD)ac = 35 μW/cm <sup>2</sup> ; Chip, TO18-4F TO18-4L		400 2800		A/W A/W
211	fc	Bandpass Center Frequency	RL = 1 kΩ, CL = 20 pF RL = 10 kΩ, CL = 20 pF		140 120		kHz kHz
212	fhc	Upper Cut-off Frequency (-3 dB)	RL = 1 kΩ, CL = 20 pF	1	400		kHz
			RL = $10 k\Omega$ , CL = $20 pF$		360		kHz



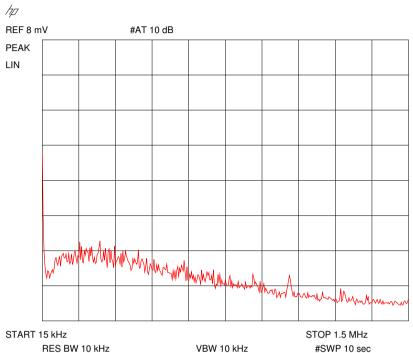
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# **ELECTRICAL CHARACTERISTICS**

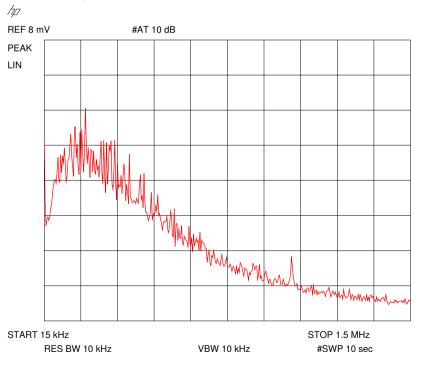
#### Operating Conditions: VCC = 4.5...13.2 V, RL = 10 k $\Omega$ , CL = 20 pF, $\lambda$ = 875 nm, Tj = -25...125 °C, if not otherwise stated.

ltem	Symbol	Parameter	Conditions				Unit
No.				Min.	Тур.	Max.	
213	flc	Lower Cut-off Frequency (-3 dB)	RL = 1 kΩ, CL = 20 pF RL = 10 kΩ, CL = 20 pF		40 35		kHz kHz
214	Q	Filter Q-Factor	Q = fc / (fhc - flc); RL = 1 kΩ, CL = 20 pF RL = 10 kΩ, CL = 20 pF		0.65 0.65		
215	G100	LF Suppression	f= 100 Hz		60		dB
216	Vn()	Output Noise Voltage (RMS)	VCC = 5 V, E(PD) = 0 VCC = 5 V, Ev(PD)dc ca. 15.000 lx, standard illuminant A, T = 2856 K, chip		7 20		mV mV
217	ton(VCC)	Power-On Setup Time	Tj = -2570 °C			450	μs









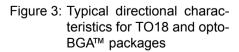


Figure 4: Output voltage noise [mV/ $\sqrt{10 \text{ kHz}}$ ] to 10 k $\Omega/20 \text{ pF}$  load with Ev()dc ca. 15.000 lx (standard illuminant A, T = 2856 K)

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> 30 20 10

> > 400

30

60

800 1000 nm

0°

10∕flat

optoBGA

20

30°

60°

Figure 1: Typical relative spectral sensitivity

**FO-lens** 0.8

0.6

0.4

600

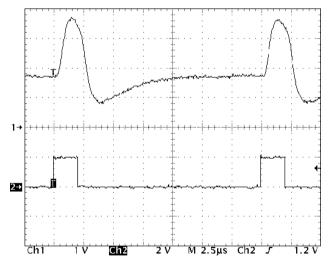


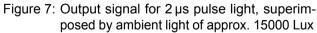


# **Example Output Signals**

Figure 5: Output signal for 2 µs pulse light.

Figure 5: Output signal for 2 μs pulse light. Transmitter: LED 875 nm with tr = tf = 0.1 μs; VCC = 5 V, RL = 10 kΩ, CL = 20 pF; Chan 1: V(OUT), 1 V/DIV vertically, Chan 2: I(LED), 20 mA/DIV vertically





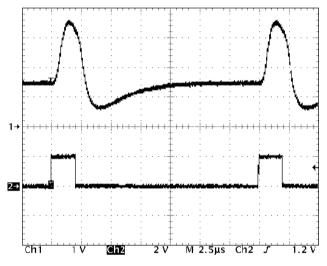


Figure 6: Output signal for 2 µs pulse light with noise (accumulated over 256 samples)

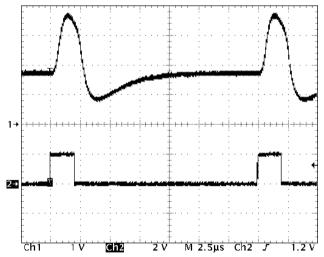
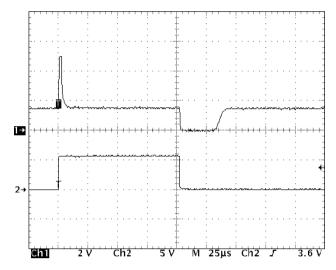


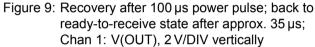
Figure 8: As in Fig. 7, accumulated for visibility over 256 samples. Despite of bright ambient light condition noise remains low level.





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### **REVISION HISTORY**

Rel.	Rel. Date*	Chapter	Modification	Page
C1	2016-05-20	PACKAGING INFORMATION	Package Dimensions for cDFN6-3x3 added	4
		THERMAL DATA	Operating Ambient Temperatur for cDFN6-3x3 reduced to 0 to 70 °C	5

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#### **ORDERING INFORMATION**

Туре	Package	Order Designation
iC-LQNP	TO18-4L	iC-LQNP TO18-4L
iC-LQNP	TO18-4F	iC-LQNP TO18-4F
iC-LQNP	cDFN6	iC-LQNP cDFN6
iC-LQNP	oBGA LQ1C	iC-LQ oBGA LQ1C
iC-LQNP	-	iC-LQNP chip

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